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NOVELTY

C2002-101854

Phase shift mask

SAMSUNG ELECTRONICS COLTD

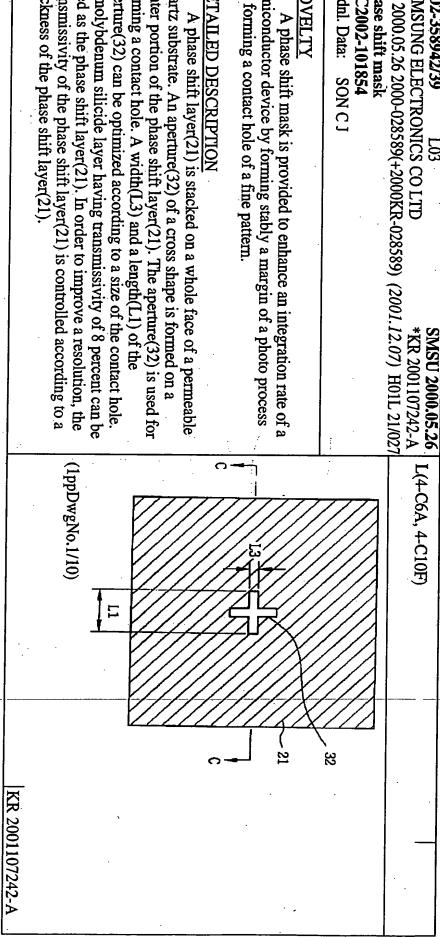
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for forming a contact hole of a fine pattern. semiconductor device by forming stably a margin of a photo process A phase shift mask is provided to enhance an integration rate of a

## DETAILED DESCRIPTION

transmissivity of the phase shift layer(21) is controlled according to a quartz substrate. An aperture (32) of a cross shape is formed on a thickness of the phase shift layer(21). used as the phase shift layer(21). In order to improve a resolution, the A molybdenum silicide layer having transmissivity of 8 percent can be aperture (32) can be optimized according to a size of the contact hole. center portion of the phase shift layer(21). The aperture(32) is used for forming a contact hole. A width(L3) and a length(L1) of the A phase shift layer(21) is stacked on a whole face of a permeable



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